

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|---|---|------------------|---------|------------------|
| S7 | 4 | ((("6475905") or ("6066569"))).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2006/06/25 03:01 |
| S8 | 883 | (257/635 or 257/637).ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/06/25 03:07 |
| S10 | 675 | (257/640 or 257/643).ccls. and @ad<"20030711" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/06/25 03:09 |
| S9 | 785 | (257/635 or 257/637).ccls. and @ad<"20030711" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/06/25 03:09 |
| S12 | 678 | (257/758).ccls. and @ad<"20030711" and (barrier with (dielectric or insulat\$4 or ILD or IMD)) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/06/25 03:10 |
| S11 | 3050 | (257/758).ccls. and @ad<"20030711" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/06/25 03:10 |
| S13 | 240 | (257/759.ccls. or 257/760.ccls.) and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:11 |
| S14 | 206 | (257/759.ccls. or 257/760.ccls.) and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:12 |
| S16 | 12858 | semiconductor and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:20 |

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|-----|-------|--|---|----|----|------------------|
| S15 | 110 | (257/773).cccls. and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:20 |
| S18 | 1740 | semiconductor and (polyimide) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:21 |
| S17 | 12833 | semiconductor and (polyimide) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:21 |
| S19 | 1023 | semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 03:24 |
| L1 | 28 | semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" and (plug or conductor or via or contact) with (polysilicon and copper and tungsten) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 17:32 |
| L2 | 5 | semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" and (plug or conductor or via or contact) with (polysilicon and copper and tungsten) and (bit adj line or bitline with contact) and (memory or dram) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/25 17:33 |